INFORMATION DISCLOSURE CITATION PTO-1449	Customer Number: 26615	ATTORNEY'S DKT NO. H1442	APPLICATION NO. ~~Unassigned~~ 10/728,910
		APPLICANT(S) Wiley Eugene Hill et al.	
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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
TH	4,996,574	02-26-91	Shirasaki	357	23.7	06-30-89

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes	Translation No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TH	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.
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TH	Co-pending U.S. Application Serial No. 10/638,334, filed August 12, 2003, entitled: "Systems and Methods for Forming Dense N-Channel and P-Channel Fins Using Shadow Implantation," 16 page specification, 18 sheets of drawings.
TH	Co-pending U.S. Application Serial No. 10/429,697, filed May 6, 2003, entitled: "FinFET-Based SRAM Cell," 16 page specification, 12 sheets of drawings.

EXAMINER	DATE CONSIDERED
TH TH HO	OCT 04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).